

NSPM0101

ESD Protection Diode

Features

- Protection for the following IEC Standards:
 - IEC61000–4–2 Level 4: ± 30 kV Contact Discharge
 - IEC61000–4–5 (Lightning) 60 A (8/20 μ s)
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

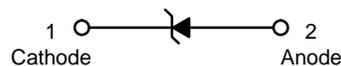
Rating	Symbol	Value	Unit
IEC 61000–4–2 (ESD) Contact Air		± 30 ± 30	kV
Operating Junction and Storage Temperature Range	T_J, T_{stg}	–65 to +150	$^{\circ}\text{C}$
Maximum Peak Pulse Current 8/20 μ s @ $T_A = 25^{\circ}\text{C}$	I_{PP}	60	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor[®]

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UDFN2
CASE 517CZ

MARKING DIAGRAM



E = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NSPM0101MUT5G	UDFN2 (Pb–Free)	8000 / Tape & Reel

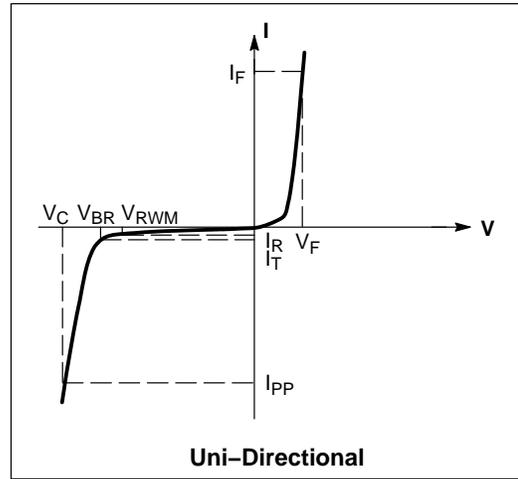
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				10	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{ mA}$	12			V
Reverse Leakage Current	I_R	$V_{RWM} = 10\text{ V}$			0.5	μA
Clamping Voltage (Note 1)	V_C	$I_{PP} = 10\text{ A}$			15	V
Clamping Voltage (Note 1)	V_C	$I_{PP} = 60\text{ A}$			20	V
Dynamic Resistance	R_{DYN}	100 ns TLP Pulse, I/O Pin to GND		0.05		Ω
Junction Capacitance	C_J	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$			400	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Non-repetitive current pulse at $T_A = 25^\circ\text{C}$, per IEC61000-4-5 waveform.

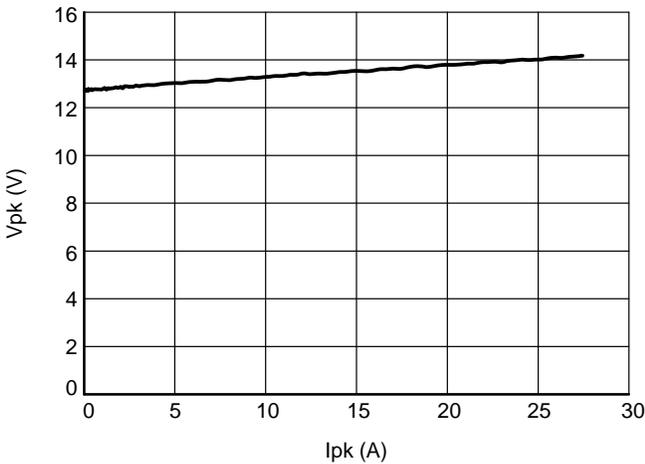


Figure 1. Positive TLP I-V Curve

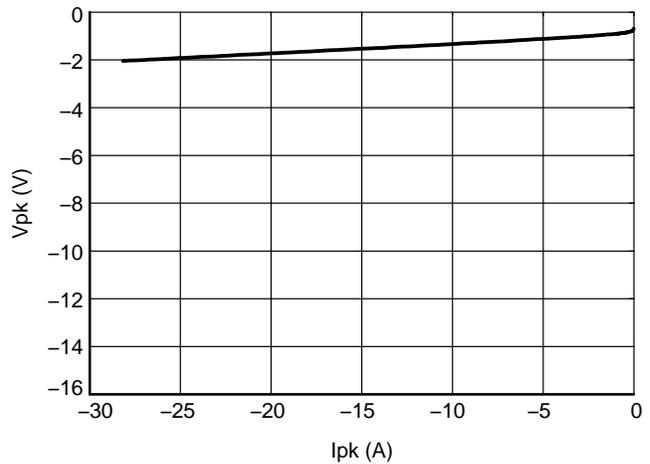


Figure 2. Negative TLP I-V Curve

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

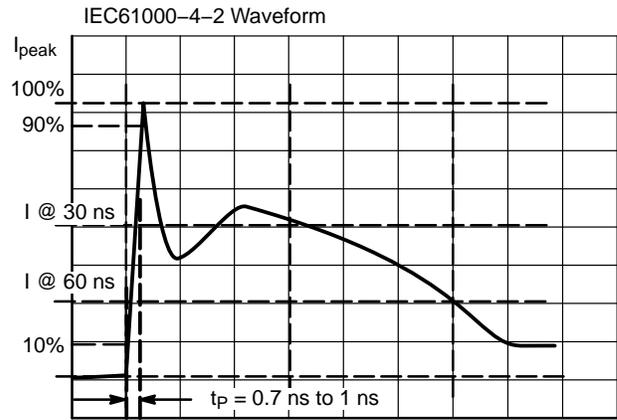


Figure 3. IEC61000-4-2 Spec

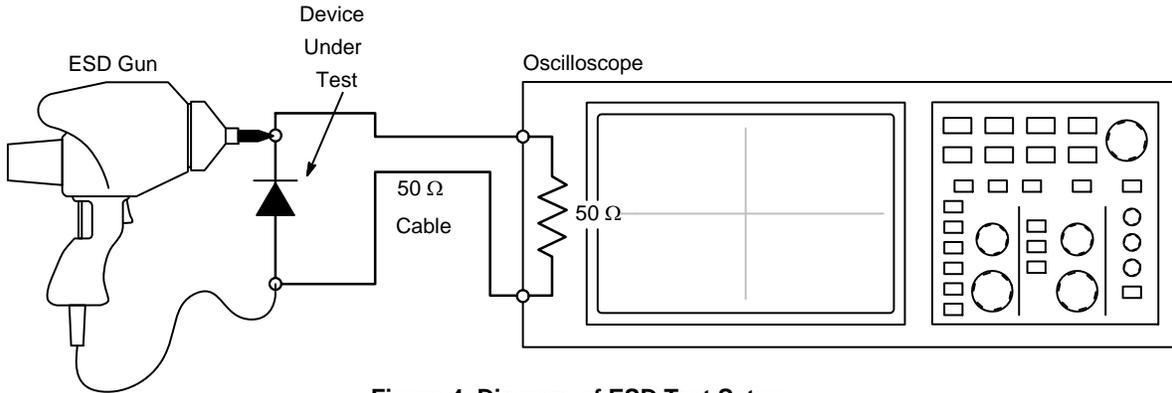


Figure 4. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

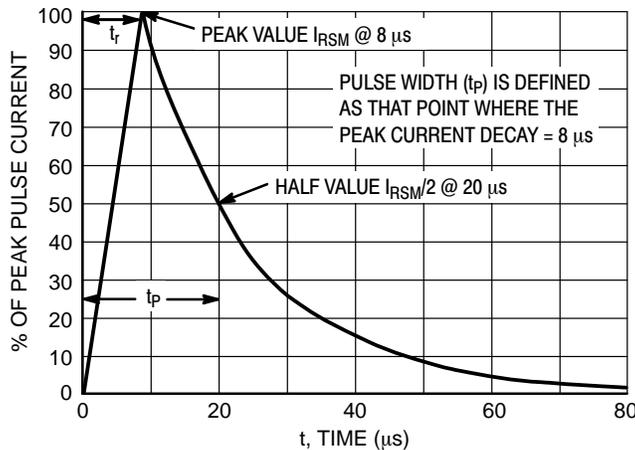


Figure 5. 8 x 20 μs Pulse Waveform

